

#### Operando X-ray Absorption Spectroscopy for the study of charge transfer in electrodes for photo-electrochemical water oxidation

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#### Layout

- Energy Sources
- Photo Electrochemical Water Splitting
- XAS
- Operando XAS experiments



#### Energy sources

# Energy production

- Up to now based mainly on (hydro)carbon(s)
- Environmental issues
  - CO<sub>2</sub> production -> greenhouse gas
    - (US-2009: 1GTon/y coal -> 3GTon/y CO<sub>2</sub>)
  - Pollutants production
    - (US-2009: 1GTon/y coal -> 92 MTon/y ashes, www.epri.com)
  - Transport risks
    - Amoco-Cadiz, Exxon-Valdez, ...
- Geopolitical issues
  - Dependence upon (sometimes embarrassing) producers
- Limited amount



World total primary energy consumption by fuel in 2020<sup>[6]</sup>



#### Source Wikipedia/BP

### Renewable energies



Sources of Energy for the Earth's Atmosphere

Source: Solar Radiation	Energy Flux	Solar
TSI (mostly Visible & Infrared)	1366 W/m <sup>2</sup>	1.2 W
MUV (200-300 nm)	15.4 W/m <sup>2</sup>	0.17 V
FUV (126-200 nm)	50 mW/m <sup>2</sup>	15 m\
EUV (0-125 nm)	10 mW/m <sup>2</sup>	10 m\

- Mainly Solar-based
- Limited power (≈1kW/m<sup>2</sup> at ground level)
- Daytime, geographic position and seasonal variations
- Need of storing the excess energy produced
  - Electrical, mechanical forms
  - Chemicals (H<sub>2</sub>)

#### Solar Irradiance, Nasa.gov



# H<sub>2</sub> as energy source

- Energy content 33kWh/kg
  - same as 1 Diesel Gallon Equivalent. Source afdc.energy.gov
- Easily stocked
  - though... density 63g/L @ 700 Bar, RT
- Useable in combustion engines and fuel cells.
- No Greenhouse gas production.
- Obtained from a widely abundant source
  - Water

# Water photo-hydrolysis

- Semiconductor based
- Min. potential: 1.23 V  $\leftrightarrow \lambda$ =1  $\mu$ m
- Multi-junction stacks
- p-doped semiconductor
  - Cathode, emits e<sup>-</sup>
  - Reduction process
  - $2e^{-}+2H^{+} \rightarrow H_{2}$
- n-doped semiconductor
  - Anode, grabs e<sup>-</sup>
  - Oxidation process
  - $2h^+ + H_2O \rightarrow \frac{1}{2}O_2 + 2H^+$



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# Horizon Europe Program





Research on renewables is a key topic for Europe



### X-ray Absorption Spectroscopy



$$\mu(\omega) = \frac{2\hbar}{\epsilon_0 \omega A_0^2} n W_{if}$$

Absorption coefficient

$$W_{if} = \frac{2\pi}{\hbar} |\langle f | \hat{H}_{Int} | i \rangle|^2 \rho(E_f)$$
 Transition probabilities

$$\hat{H}_{Int} = i\hbar \vec{A} \left( \vec{r} 
ight) \cdot \vec{p}$$
 Electricites intera

Electron – photon interaction Hamiltonian



$$\vec{A} = |A_0|\vec{\epsilon}e^{i\vec{k}\cdot\vec{r}} \approx |A_0|\vec{\epsilon}\left(1+i\vec{k}\cdot\vec{r}-\dots\right) \approx |A_0|\vec{\epsilon}(1)$$

Dipole approximation == kr << 1

$$ec{p}=-i\hbarec{
abla}~ec{
abla}=rac{m\omega}{\hbar}ec{r}$$
 From QM identities

$$W_{if} = \frac{\pi\hbar e^2}{m^2} |A_0|^2 \sum_f |\langle f|\vec{\epsilon} \cdot \vec{r_j}|i\rangle|^2 \delta\left(E_f - E_i - \hbar\omega\right)$$

Dependence on the photon polarization



$$\langle f|\hat{H}_{Int}|i\rangle = \left(\int_{\Omega}\dots\partial\Omega\right)\int_{\vec{r}}f\hat{H}_{Int}i\partial\vec{r}$$

Angular nart

is, 2s 2p states (K, L<sub>I</sub>, L<sub>II, III</sub> edges) Nonzero only in a restricted region around the nucleus Valid dipole approx. More marked interference effect



Radial nart



Rehr, RMP 2000

- Being |i> nonzero only in a restricted region the integral <f|H|i> depends on the amplitude of <f| on the absorbing atom.
- Interference with other (phase coherent) scattered waves
- The maxima and minima in <f| determine the oscillations above the edge.

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<f | must obey the selection rules  $\Delta L = \pm 1$ In practice we have s —> p and p—> d transitions

#### ISTITUTO OFFICINA DEI MATERIALI XANES & EXAFS **EXAFS XANES** Co3040301.dat 1.5 H EXAFS XANES High E photoelectrons Low E photoelectrons $\lambda_{phel} < R_{interatomic}$ Local structure $\lambda_{\text{phel}} > R_{\text{interatomic}}$ Symmetry norm ×µ(E) R @ 1% Valence state N@ 10% Semi-quantitative 0.5 0 7700 7800 7900 8000 8100 E (eV)

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#### Formulas



$$\chi(k) = \sum_{j=shells} S_0^2 \frac{N_j}{kR_j^2} f_j^{eff}(k) e^{\frac{-2R_j}{\lambda}} \sin(2kR_j + \phi_j^{tot}(k)) e^{-2k^2\sigma_j^2}$$

High Photoelectron energy (~ 100 – 2000 eV)

- MS approach
- == EXAFS region

$$\mu(E) \propto \lim_{\eta \to 0^+} \Im\left( \langle i | \vec{\epsilon} \cdot \vec{r} \frac{1}{E - H - i\eta} \vec{\epsilon} \cdot \vec{r} | i \rangle \right)$$

Low photoelectron energy (~0-100 eV)

- FMS approach
- == XANES region

# Valence state from XANES

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The valence state can be estimated from the edge position



# Local symmetry from XANES





- Appear on the K edge of 3d metals
- Due to 1s-3d (semi-forbidden) transitions
- Well visible in non-centrosymmetric environments





#### Data collection modes

# Measuring $\boldsymbol{\mu}$ direct method





### Indirect mode







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A. Fujishima, K. Honda Nature 238 (1972), 37

# Experimental Examples



Letter

pubs.acs.org/ac



dx.doi.org/10.1021/ac401414v | Anal. Chem. 2013, 85, 7009-7013

#### Fixed Energy X-ray Absorption Voltammetry

Alessandro Minguzzi,<sup>\*,†</sup> Ottavio Lugaresi,<sup>†</sup> Cristina Locatelli,<sup>†</sup> Sandra Rondinini,<sup>†</sup> Francesco D'Acapito,<sup>‡</sup> Elisabetta Achilli,<sup>§</sup> and Paolo Ghigna<sup>§</sup>

Site – selective voltammetry

XAS-based  $IrO_x$  films in an Electrochemical cell  $Ir-L_3$  edge



#### Fixed Energy X-ray Absorption Voltammetry





#### With XAS we see the contribution of an element to the total voltammetric response



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# Observation of charge transfer cascades in $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/IrO<sub>x</sub> photoanodes by operando X-ray absorption spectroscopy<sup>†</sup>



Alessandro Minguzzi,\*<sup>ab</sup> Alberto Naldoni,<sup>c</sup> Ottavio Lugaresi,‡<sup>a</sup> Elisabetta Achilli,<sup>d</sup> Francesco D'Acapito,<sup>e</sup> Francesco Malara,<sup>c</sup> Cristina Locatelli,<sup>ab</sup> Alberto Vertova,<sup>abc</sup> Sandra Rondinini<sup>abc</sup> and Paolo Ghigna<sup>bd</sup>



Is Ir really an efficient hole collector ?





Difference of spectra Light-Dark Nothing happens up to 0.8 V (remember: water splits at 1.23 V) Big increase of the WL at 1.4 V

WL == holes in the 5d stats of Ir





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Ke	sea	rch	Aπ	icle
1000				a bar a constant

### Direct Observation of Photoinduced Higher Oxidation States at a Semiconductor/Electrocatalyst Junction

Francesco Malara, Martina Fracchia, Hana Kmentová, Rinaldo Psaro, Alberto Vertova, Danilo Oliveira de Souza, Giuliana Aquilanti, Luca Olivi, Paolo Ghigna,\* Alessandro Minguzzi,\* and Alberto Naldoni\*







Difference spectra L-D in various potential conditions

FEXRAV L-D at constant potential

#### Also for Ni: observation of transfer of holes in the NiOx layer

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Operando and Time-Resolved X-Ray Absorption Spectroscopy for the Study of Photoelectrode Architectures

Tomasz Baran<sup>a</sup>, Martina Fracchia<sup>b</sup>, Alberto Vertova<sup>a,c,d,1</sup>, Elisabetta Achilli<sup>b</sup>, Alberto Naldoni<sup>c</sup>, Francesco Malara<sup>c</sup>, Giacomo Rossi<sup>e</sup>, Sandra Rondinini<sup>a,c,d,1</sup>, Paolo Ghigna<sup>b,d</sup>, Alessandro Minguzzi<sup>a,d,\*,1</sup>, Francesco D'Acapito<sup>f</sup>





#### The charge transfer goes on for about 600 ns Limited effect due to low laser power

### Conclusion



- Need of understanding light-matter phenomena in order to develop renewable energy sources
- XAS is a technique that permits the speciation of elements also in time resolved mode
- Evidence of hole transfer from the semiconductor to the coating oxide.